

Hitoshi Habuka

List of Publications by Year in descending order

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156
papers

1,311
citations

471371

17
h-index

552653

26
g-index

156
all docs

156
docs citations

156
times ranked

362
citing authors

| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 1 | Model on transport phenomena and epitaxial growth of silicon thin film in SiHCl ₃ -H ₂ system under atmospheric pressure. Journal of Crystal Growth, 1996, 169, 61-72. | 0.7 | 89 |
| 2 | Chemical process of silicon epitaxial growth in a SiHCl ₃ -H ₂ system. Journal of Crystal Growth, 1999, 207, 77-86. | 0.7 | 56 |
| 3 | Modeling of Epitaxial Silicon Thin-Film Growth on a Rotating Substrate in a Horizontal Single-Wafer Reactor. Journal of the Electrochemical Society, 1995, 142, 4272-4278. | 1.3 | 37 |
| 4 | Dominant rate process of silicon surface etching by hydrogen chloride gas. Thin Solid Films, 2005, 489, 104-110. | 0.8 | 35 |
| 5 | Adsorption and Desorption Rate of Multicomponent Organic Species on Silicon Wafer Surface. Journal of the Electrochemical Society, 2001, 148, G365. | 1.3 | 33 |
| 6 | Roughness of Silicon Surface Heated in Hydrogen Ambient. Journal of the Electrochemical Society, 1995, 142, 3092-3098. | 1.3 | 32 |
| 7 | Nonlinear increase in silicon epitaxial growth rate in a SiHCl ₃ -H ₂ system under atmospheric pressure. Journal of Crystal Growth, 1997, 182, 352-362. | 0.7 | 32 |
| 8 | Silicon Carbide Etching Using Chlorine Trifluoride Gas. Japanese Journal of Applied Physics, 2005, 44, 1376-1381. | 0.8 | 32 |
| 9 | Rate Theory of Multicomponent Adsorption of Organic Species on Silicon Wafer Surface. Journal of the Electrochemical Society, 2000, 147, 2319. | 1.3 | 30 |
| 10 | Silicon epitaxial growth process using trichlorosilane gas in a single-wafer high-speed substrate rotation reactor. Journal of Crystal Growth, 2011, 327, 1-5. | 0.7 | 29 |
| 11 | Temperature-Dependent Behavior of 4H-Silicon Carbide Surface Morphology Etched Using Chlorine Trifluoride Gas. Journal of the Electrochemical Society, 2009, 156, H971. | 1.3 | 27 |
| 12 | Airborne Organic Contamination Behavior on Silicon Wafer Surface. Journal of the Electrochemical Society, 2003, 150, G148. | 1.3 | 24 |
| 13 | Determination of Etch Rate Behavior of 4H-SiC Using Chlorine Trifluoride Gas. Japanese Journal of Applied Physics, 2007, 46, 7875. | 0.8 | 24 |
| 14 | Heat Transport Analysis for Flash Lamp Annealing. Japanese Journal of Applied Physics, 2007, 46, 937-942. | 0.8 | 22 |
| 15 | Numerical Evaluation of Silicon-Thin Film Growth from SiHCl ₃ -H ₂ Gas Mixture in a Horizontal Chemical Vapor Deposition Reactor. Japanese Journal of Applied Physics, 1994, 33, 1977-1985. | 0.8 | 20 |
| 16 | Development of Evaluation Method for Organic Contamination on Silicon Wafer Surfaces. Journal of the Electrochemical Society, 2001, 148, G644. | 1.3 | 20 |
| 17 | Polycrystalline silicon carbide film deposition using monomethylsilane and hydrogen chloride gases. Journal of Crystal Growth, 2007, 300, 374-381. | 0.7 | 18 |
| 18 | Silicon carbide film deposition at low temperatures using monomethylsilane gas. Surface and Coatings Technology, 2010, 204, 1432-1437. | 2.2 | 18 |

| # | ARTICLE | IF | CITATIONS |
|----|--|-----|-----------|
| 19 | Silicon Etch Rate Using Chlorine Trifluoride. <i>Journal of the Electrochemical Society</i> , 2004, 151, G783. | 1.3 | 17 |
| 20 | In Situ Cleaning Process of Silicon Carbide Epitaxial Reactor. <i>ECS Journal of Solid State Science and Technology</i> , 2015, 4, P137-P140. | 0.9 | 16 |
| 21 | Reaction of Hydrogen Fluoride Gas at High Temperatures with Silicon Oxide Film and Silicon Surface. <i>Japanese Journal of Applied Physics</i> , 1998, 37, 6123-6127. | 0.8 | 15 |
| 22 | High-Performance Silicon Etching Using Chlorine Trifluoride Gas. <i>Journal of the Electrochemical Society</i> , 2003, 150, G461. | 1.3 | 15 |
| 23 | Time-Dependent Airborne Organic Contamination on Silicon Wafer Surface Stored in a Plastic Box. <i>Japanese Journal of Applied Physics</i> , 2003, 42, 1575-1580. | 0.8 | 15 |
| 24 | A Direct Approach for Evaluating the Thermal Condition of a Silicon Substrate under Infrared Rays and Specular Reflectors. <i>Journal of the Electrochemical Society</i> , 1999, 146, 713-718. | 1.3 | 14 |
| 25 | Cleaning Process Applicable to Silicon Carbide Chemical Vapor Deposition Reactor. <i>ECS Journal of Solid State Science and Technology</i> , 2014, 3, N3006-N3009. | 0.9 | 14 |
| 26 | Repetition of In Situ Cleaning Using Chlorine Trifluoride Gas for Silicon Carbide Epitaxial Reactor. <i>ECS Journal of Solid State Science and Technology</i> , 2016, 5, P12-P15. | 0.9 | 14 |
| 27 | In situ cleaning method for silicon surface using hydrogen fluoride gas and hydrogen chloride gas in a hydrogen ambient. <i>Journal of Crystal Growth</i> , 1998, 186, 104-112. | 0.7 | 13 |
| 28 | Dominant Forces for Driving Bubbles in a Wet Cleaning Bath Using Megasonic Wave. <i>Journal of the Electrochemical Society</i> , 2010, 157, H585. | 1.3 | 13 |
| 29 | Water Motion over a Wafer Surface Rotating in a Single-Water Wet Cleaner. <i>Journal of the Electrochemical Society</i> , 2011, 158, H487. | 1.3 | 13 |
| 30 | By-Product Formation in a Trichlorosilane-Hydrogen System for Silicon Film Deposition. <i>ECS Journal of Solid State Science and Technology</i> , 2015, 4, P16-P19. | 0.9 | 13 |
| 31 | Quartz Crystal Microbalance for Silicon Surface Organic Contamination. <i>Journal of the Electrochemical Society</i> , 2005, 152, G241. | 1.3 | 12 |
| 32 | Etch rate and surface morphology of polycrystalline β -silicon carbide using chlorine trifluoride gas. <i>Thin Solid Films</i> , 2006, 514, 193-197. | 0.8 | 12 |
| 33 | Quick Cleaning Process for Silicon Carbide Chemical Vapor Deposition Reactor. <i>ECS Journal of Solid State Science and Technology</i> , 2017, 6, P526-P530. | 0.9 | 12 |
| 34 | Metal Fluorides Produced Using Chlorine Trifluoride Gas. <i>Journal of Surface Engineered Materials and Advanced Technology</i> , 2015, 05, 228-236. | 0.2 | 12 |
| 35 | Instability of diborane gas in silicon epitaxial film growth. <i>Journal of Crystal Growth</i> , 2000, 209, 807-815. | 0.7 | 11 |
| 36 | Molecular Interaction Radii and Rate Constants for Clarifying Organic Compound Physisorption on Silicon Surface. <i>Journal of the Electrochemical Society</i> , 2010, 157, H1014. | 1.3 | 11 |

| # | ARTICLE | IF | CITATIONS |
|----|--|-----|-----------|
| 37 | Mechanism of Silicon Carbide Film Deposition at Room Temperature Using Monomethylsilane Gas. Journal of the Electrochemical Society, 2011, 158, H352. | 1.3 | 11 |
| 38 | Chemical vapor deposition of amorphous silicon carbide thin films on metal surfaces using monomethylsilane gas at low temperatures. Surface and Coatings Technology, 2013, 217, 88-93. | 2.2 | 11 |
| 39 | Surface Chemical Reaction Model of Silicon Dioxide Film Etching by Dilute Hydrogen Fluoride Using a Single Wafer Wet Etcher. ECS Journal of Solid State Science and Technology, 2013, 2, P264-P267. | 0.9 | 11 |
| 40 | Water Motion in Carrierless Wet Station. Journal of the Electrochemical Society, 2004, 151, G814. | 1.3 | 10 |
| 41 | 4H Silicon Carbide Etching Using Chlorine Trifluoride Gas. Materials Science Forum, 0, 600-603, 655-658. | 0.3 | 10 |
| 42 | Etching Rate of Silicon Dioxide Using Chlorine Trifluoride Gas. Japanese Journal of Applied Physics, 2009, 48, 026504. | 0.8 | 10 |
| 43 | Non-heat assistance chemical vapor deposition of amorphous silicon carbide using monomethylsilane gas under argon plasma. Surface and Coatings Technology, 2016, 285, 255-261. | 2.2 | 10 |
| 44 | Advantages of a slim vertical gas channel at high SiHCl ₃ concentrations for atmospheric pressure silicon epitaxial growth. Materials Science in Semiconductor Processing, 2018, 87, 13-18. | 1.9 | 10 |
| 45 | Gas flow and heat transfer in a pancake chemical vapor deposition reactor. Journal of Crystal Growth, 1995, 151, 375-383. | 0.7 | 9 |
| 46 | Dominant Overall Chemical Reaction in a Chlorine Trifluoride-Silicon-Nitrogen System at Atmospheric Pressure. Japanese Journal of Applied Physics, 1999, 38, 6466-6469. | 0.8 | 9 |
| 47 | Gas Velocity Influence on Silicon Surface Organic Contamination Evaluated Using Quartz Crystal Microbalance. Journal of the Electrochemical Society, 2005, 152, G862. | 1.3 | 9 |
| 48 | Physisorption and Desorption of Diethyl Phthalate and Isopropanol on a Silicon Surface. Journal of the Electrochemical Society, 2007, 154, H1031. | 1.3 | 9 |
| 49 | 4H-SiC Surface Morphology Etched Using ClF ₃ Gas. Materials Science Forum, 2010, 645-648, 787-790. | 0.3 | 9 |
| 50 | Numerical calculation model of a single wafer wet etcher using a swinging nozzle. Materials Science in Semiconductor Processing, 2012, 15, 543-548. | 1.9 | 9 |
| 51 | Langasite crystal microbalance frequency behavior over wide gas phase conditions for chemical vapor deposition. Surface and Coatings Technology, 2013, 230, 312-315. | 2.2 | 9 |
| 52 | Silicon Chemical Vapor Deposition Process Using a Half-Inch Silicon Wafer for Minimal Manufacturing System. Physics Procedia, 2013, 46, 230-238. | 1.2 | 9 |
| 53 | Susceptor Coating Materials Applicable for SiC Reactor Cleaning. Materials Science Forum, 2017, 897, 99-102. | 0.3 | 9 |
| 54 | Thermal Conditions in Rapid Thermal Processing System Using Circular Infrared Lamp. Journal of the Electrochemical Society, 2000, 147, 4660. | 1.3 | 8 |

| # | ARTICLE | IF | CITATIONS |
|----|--|-----|-----------|
| 55 | Design of a Rapid Thermal Processing System Using a Reflection-Resolved Ray Tracing Method. Journal of the Electrochemical Society, 2001, 148, G543. | 1.3 | 8 |
| 56 | Formation mechanism of local thickness profile of silicon epitaxial film. Journal of Crystal Growth, 2004, 266, 327-332. | 0.7 | 8 |
| 57 | Etching Rate Behavior of 4H-Silicon Carbide Using Chlorine Trifluoride Gas. ECS Transactions, 2008, 13, 39-52. | 0.3 | 8 |
| 58 | Room temperature process for chemical vapor deposition of amorphous silicon carbide thin film using monomethylsilane gas. Surface and Coatings Technology, 2011, 206, 1503-1506. | 2.2 | 8 |
| 59 | Chlorine Trifluoride Gas Transport and Etching Rate Distribution in Silicon Carbide Dry Etcher. Materials Science Forum, 0, 821-823, 553-556. | 0.3 | 8 |
| 60 | Increase in silicon film deposition rate in a SiHCl ₃ -SiH _x -H ₂ system. Journal of Crystal Growth, 2017, 468, 204-207. | 0.7 | 8 |
| 61 | Flatness Deterioration of Silicon Epitaxial Film Formed Using Horizontal Single-Wafer Epitaxial Reactor. Japanese Journal of Applied Physics, 2001, 40, 6041-6044. | 0.8 | 7 |
| 62 | Langasite Crystal Microbalance Used for In-Situ Monitoring of Amorphous Silicon Carbide Film Deposition. ECS Journal of Solid State Science and Technology, 2012, 1, P62-P65. | 0.9 | 7 |
| 63 | Density of Etch Pits on C-Face 4H-SiC Surface Produced by ClF ₃ Gas. Materials Science Forum, 0, 725, 49-52. | 0.3 | 7 |
| 64 | Development of Silicon Carbide Dry Etcher Using Chlorine Trifluoride Gas. Materials Science Forum, 0, 778-780, 738-741. | 0.3 | 7 |
| 65 | Reflector Influence on Rapid Heating of Minimal Manufacturing Chemical Vapor Deposition Reactor. ECS Journal of Solid State Science and Technology, 2016, 5, P280-P284. | 0.9 | 7 |
| 66 | Mirror Etching of Single Crystalline C-Face 4H-Silicon Carbide Wafer by Chlorine Trifluoride Gas. ECS Journal of Solid State Science and Technology, 2017, 6, P582-P585. | 0.9 | 7 |
| 67 | Exposure of Tantalum Carbide, Silicon Nitride and Aluminum Nitride to Chlorine Trifluoride Gas. ECS Journal of Solid State Science and Technology, 2019, 8, P175-P179. | 0.9 | 7 |
| 68 | Haze Generation on Silicon Surface Heated in Hydrogen Ambient at Atmospheric Pressure. Journal of the Electrochemical Society, 1997, 144, 3261-3265. | 1.3 | 6 |
| 69 | Change in Microroughness of a Silicon Surface during In Situ Cleaning Using HF and HCl Gases. Journal of the Electrochemical Society, 1998, 145, 4264-4271. | 1.3 | 6 |
| 70 | Model of boron incorporation into silicon epitaxial film in a B ₂ H ₆ -SiHCl ₃ -H ₂ system. Journal of Crystal Growth, 2001, 222, 183-193. | 0.7 | 6 |
| 71 | Flatness Deterioration of Silicon Epitaxial Film Formed in a Horizontal Single-Wafer Epitaxial Reactor II. Japanese Journal of Applied Physics, 2002, 41, 5692-5696. | 0.8 | 6 |
| 72 | Density and Behavior of Etch Pits on C-Face 4H-SiC Surface Produced by ClF ₃ Gas. Materials Science Forum, 2012, 717-720, 379-382. | 0.3 | 6 |

| # | ARTICLE | IF | CITATIONS |
|----|--|-----|-----------|
| 73 | Transport phenomena in a slim vertical atmospheric pressure chemical vapor deposition reactor utilizing natural convection. <i>Materials Science in Semiconductor Processing</i> , 2017, 71, 348-351. | 1.9 | 6 |
| 74 | Non-Heat Assistance Plasma-Enhanced Chemical Vapor Deposition of SiC _x NyOz Film Using Monomethylsilane, Nitrogen and Argon. <i>ECS Journal of Solid State Science and Technology</i> , 2017, 6, P443-P448. | 0.9 | 6 |
| 75 | Real time evaluation of silicon epitaxial growth process by exhaust gas measurement using quartz crystal microbalance. <i>Materials Science in Semiconductor Processing</i> , 2018, 88, 192-197. | 1.9 | 6 |
| 76 | Deposition and etching behaviour of boron trichloride gas at silicon surface. <i>Journal of Crystal Growth</i> , 2020, 529, 125301. | 0.7 | 6 |
| 77 | Slim Water Injection Nozzle for Silicon Wafer Wet Cleaning Bath. <i>Advances in Chemical Engineering and Science</i> , 2016, 06, 345-354. | 0.2 | 6 |
| 78 | Effect of Transport Phenomena on Boron Concentration Profiles in Silicon Epitaxial Wafers. <i>Journal of the Electrochemical Society</i> , 1996, 143, 677-682. | 1.3 | 5 |
| 79 | Hot-wall and cold-wall environments for silicon epitaxial film growth. <i>Journal of Crystal Growth</i> , 2001, 223, 145-155. | 0.7 | 5 |
| 80 | Heat Balance Evaluation for Rapid Thermal Processing System Design. <i>Journal of the Electrochemical Society</i> , 2005, 152, G924. | 1.3 | 5 |
| 81 | Decarbonation and Pore Structural Change of Ca-Solid Reactant for CaO/CO ₂ Chemical Heat Pump. <i>Journal of Chemical Engineering of Japan</i> , 2008, 41, 513-518. | 0.3 | 5 |
| 82 | Langasite Crystal Microbalance for Development of Reactive Surface Preparation of Silicon Carbide Film Deposition from Monomethylsilane Gas. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 096505. | 0.8 | 5 |
| 83 | Surface and gas phase reactions induced in a trichlorosilane-SiH _x system for silicon film deposition. <i>Surface and Coatings Technology</i> , 2015, 272, 273-277. | 2.2 | 5 |
| 84 | In Situ Measurement for Evaluating Temperature Change Related to Silicon Film Formation in a SiHCl ₃ -H ₂ System. <i>ECS Journal of Solid State Science and Technology</i> , 2016, 5, P16-P20. | 0.9 | 5 |
| 85 | A Method to Adjust Polycrystalline Silicon Carbide Etching Rate Profile by Chlorine Trifluoride Gas. <i>Materials Science Forum</i> , 0, 897, 383-386. | 0.3 | 5 |
| 86 | Parallel langmuir processes for silicon epitaxial growth in a SiHCl ₃ -SiH _x -H ₂ system. <i>Materials Science in Semiconductor Processing</i> , 2017, 72, 134-138. | 1.9 | 5 |
| 87 | Yttrium oxide film for protecting quartz glass surface from etching by long-term exposure to chlorine trifluoride gas at room temperature. <i>Materials Science in Semiconductor Processing</i> , 2018, 83, 211-215. | 1.9 | 5 |
| 88 | Nonempirical Design of Rapid Thermal Processing System. <i>Japanese Journal of Applied Physics</i> , 2001, 40, 7123-7128. | 0.8 | 4 |
| 89 | <i>in situ</i> observation of chemical vapor deposition using SiHCl ₃ and BCl ₃ gases. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2015, 12, 953-957. | 0.8 | 4 |
| 90 | Evaluation of Molecular Interaction between Organic Molecules Physisorbed on Silicon Native Oxide Surface in Dry and Humid Atmosphere. <i>ECS Journal of Solid State Science and Technology</i> , 2015, 4, P86-P90. | 0.9 | 4 |

| # | ARTICLE | IF | CITATIONS |
|-----|---|-----|-----------|
| 91 | Formation and Removal of Carbon Film on Silicon Carbide Surface Using Chlorine Trifluoride Gas. ECS Journal of Solid State Science and Technology, 2016, 5, P441-P445. | 0.9 | 4 |
| 92 | High-Temperature Reactor Cleaning Using Chlorine Trifluoride Gas for Silicon Carbide Chemical Vapor Deposition. ECS Journal of Solid State Science and Technology, 2019, 8, P400-P406. | 0.9 | 4 |
| 93 | Anticorrosive Behavior of SiC _x N _y O _z Film Formed by Non-Heat Assistance Plasma-Enhanced Chemical Vapor Deposition Using Monomethylsilane, Nitrogen and Argon Gases. ECS Journal of Solid State Science and Technology, 2020, 9, 024001. | 0.9 | 4 |
| 94 | Boron-Silicon Film Chemical Vapor Deposition Using Boron Trichloride, Dichlorosilane and Monomethylsilane Gases. ECS Journal of Solid State Science and Technology, 2021, 10, 064006. | 0.9 | 4 |
| 95 | Design of a Silicon Carbide Chemical Vapor Deposition Reactor Cleaning Process Using Chlorine Trifluoride Gas Accounting for Exothermic Reaction Heat. ECS Journal of Solid State Science and Technology, 2020, 9, 104008. | 0.9 | 4 |
| 96 | Computation Transport Phenomena in Chemical Engineering. Transport of Dopant Gas during Silicon Epitaxial Thin-Film Growth in a Horizontal Reactor.. Kagaku Kogaku Ronbunshu, 1997, 23, 772-779. | 0.1 | 3 |
| 97 | Highly Concentrated Ozone Gas for Preparing Wettable Polyimide Surface. Japanese Journal of Applied Physics, 2005, 44, 5225-5230. | 0.8 | 3 |
| 98 | Water and Bubble Motions Under Megasonic Wave in a Silicon Wafer Wet Cleaning Bath. ECS Transactions, 2009, 25, 265-272. | 0.3 | 3 |
| 99 | Low Temperature SiC Film Deposition Using Trichlorosilane Gas and Monomethylsilane Gas. Journal of Nanoscience and Nanotechnology, 2011, 11, 8374-8377. | 0.9 | 3 |
| 100 | Precipitates caused by prolonged high-temperature annealing in floating zone silicon wafer grown from Czochralski single-crystal rod. Materials Science in Semiconductor Processing, 2013, 16, 923-927. | 1.9 | 3 |
| 101 | Numerical evaluation of silicon epitaxial growth on a 450- μ m diameter substrate. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 1539-1543. | 0.8 | 3 |
| 102 | Cleaning Process for Using Chlorine Trifluoride Gas Silicon Carbide Chemical Vapor Deposition Reactor. Materials Science Forum, 2015, 821-823, 125-128. | 0.3 | 3 |
| 103 | Water Outlet Design of Wet Cleaning Bath for 300-mm Diameter Silicon Wafers. ECS Journal of Solid State Science and Technology, 2018, 7, N123-N127. | 0.9 | 3 |
| 104 | Influence of Metal and Polymer Substrate on SiC _x N _y O _z Film Formation by Non-Heat Assistance Plasma-Enhanced Chemical Vapor Deposition Using Monomethylsilane, Nitrogen and Argon Gases. ECS Journal of Solid State Science and Technology, 2019, 8, P407-P411. | 0.9 | 3 |
| 105 | Chlorine Trifluoride Gas Distributor Design for Single-Crystalline C-Face 4H-Silicon Carbide Wafer Etcher. Materials Science Forum, 0, 963, 520-524. | 0.3 | 3 |
| 106 | CVD Material Processing. Numerical Calculations of Heat Profile using Circular Infrared Lamp Heating Furnace.. Kagaku Kogaku Ronbunshu, 2000, 26, 785-791. | 0.1 | 2 |
| 107 | Air Flow in Square Quartz Plate Spin Cleaner. Japanese Journal of Applied Physics, 2005, 44, 8182-8185. | 0.8 | 2 |
| 108 | Small-Batch Reactor Development for Silicon Epitaxial Film Growth Based on Theory of Transport Phenomena. ECS Transactions, 2006, 2, 21-32. | 0.3 | 2 |

| # | ARTICLE | IF | CITATIONS |
|-----|---|-----|-----------|
| 109 | Carbonation/Decarbonation of Ca-Solid Reactant Derived from Natural Limestone for Thermal-Energy Storage and Temperature Upgrade. <i>Journal of Chemical Engineering of Japan</i> , 2007, 40, 1270-1274. | 0.3 | 2 |
| 110 | Heat Transport and Temperature Gradient in Silicon-on-Insulator Wafer during Flash Lamp Annealing Process. <i>Japanese Journal of Applied Physics</i> , 2008, 47, 6277-6281. | 0.8 | 2 |
| 111 | Hafnium Oxide Film Etching Using Hydrogen Chloride Gas. <i>Japanese Journal of Applied Physics</i> , 2009, 48, 125503. | 0.8 | 2 |
| 112 | Etch Pits on 4H-SiC Surface Produced by ClF_3 Gas. <i>Materials Science Forum</i> , 0, 679-680, 286-289. | 0.3 | 2 |
| 113 | Water Motion over a Wafer Surface Rotating in a Single-Wafer Wet Cleaner. <i>ECS Transactions</i> , 2011, 41, 279-286. | 0.3 | 2 |
| 114 | Silicon Epitaxial Growth Rate and Transport Phenomena in a Vertical Stacked-Type Multi-Wafer Reactor. <i>Japanese Journal of Applied Physics</i> , 2012, 51, 026701. | 0.8 | 2 |
| 115 | Off-Orientation Influence on C-Face (0001) 4H-SiC Surface Morphology Produced by Etching Using Chlorine Trifluoride Gas. <i>ECS Journal of Solid State Science and Technology</i> , 2013, 2, N3025-N3027. | 0.9 | 2 |
| 116 | Precipitates formed in silicon wafers by prolonged high-temperature annealing in nitrogen atmosphere. <i>Japanese Journal of Applied Physics</i> , 2014, 53, 05FJ05. | 0.8 | 2 |
| 117 | Silicon epitaxial growth accelerated by parallel Langmuir processes using SiH_2Cl_2 and SiH_3CH_3 gases. <i>Semiconductor Science and Technology</i> , 2018, 33, 094002. | 1.0 | 2 |
| 118 | Quartz crystal microbalance for real-time monitoring chlorosilane gas transport in slim vertical cold wall chemical vapor deposition reactor. <i>Materials Science in Semiconductor Processing</i> , 2020, 106, 104759. | 1.9 | 2 |
| 119 | Etching Rate Profile of C-Face 4H-SiC Wafer Depending on Total Gas Flow Rate of Chlorine Trifluoride and Nitrogen. <i>Materials Science Forum</i> , 0, 1004, 173-179. | 0.3 | 2 |
| 120 | Electric Current in Rate Equation for Parallel Plate Plasma-Enhanced Chemical Vapour Deposition of $\text{SiC}_x\text{N}_y\text{O}_z$ Film without Heat Assistance. <i>ECS Journal of Solid State Science and Technology</i> , 2020, 9, 024017. | 0.9 | 2 |
| 121 | Benzoxazine-modified BMI Heat-resistant Resin with Low Dielectric Properties. <i>Transactions of the Japan Institute of Electronics Packaging</i> , 2021, 14, E20-016-1-E20-016-14. | 0.3 | 2 |
| 122 | Langasite Crystal Microbalance for Development of Reactive Surface Preparation of Silicon Carbide Film Deposition from Monomethylsilane Gas. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 096505. | 0.8 | 2 |
| 123 | A Practical Design Method for a Rapid Thermal Processing System. <i>Japanese Journal of Applied Physics</i> , 2004, 43, 833-838. | 0.8 | 1 |
| 124 | Room Temperature Halogenation of Polyimide Film Surface using Chlorine Trifluoride Gas. <i>Japanese Journal of Applied Physics</i> , 2004, 43, 730-734. | 0.8 | 1 |
| 125 | In-Situ Measurement Method and Rate Theory for Clarifying Multi-Component Organic Compounds Adsorption and Desorption on Silicon Surface. <i>ECS Transactions</i> , 2007, 11, 363-374. | 0.3 | 1 |
| 126 | Hafnium Oxide Etching Using Hydrogen Chloride Gas. <i>ECS Transactions</i> , 2009, 19, 289-299. | 0.3 | 1 |

| # | ARTICLE | IF | CITATIONS |
|-----|---|-----|-----------|
| 127 | Atmospheric Pressure SiC Film Deposition at Low Temperatures Using SiH ₃ CH ₃ and HCl Gases. ECS Transactions, 2009, 25, 191-198. | 0.3 | 1 |
| 128 | Room Temperature Process for Chemical Vapor Deposition of Amorphous Silicon Carbide Thin Film Using Monomethylsilane Gas. Materials Research Society Symposia Proceedings, 2012, 1433, 83. | 0.1 | 1 |
| 129 | Low temperature amorphous silicon carbide thin film formation process on aluminum surface using monomethylsilane gas and trichlorosilane gas. Journal of Crystal Growth, 2014, 401, 523-526. | 0.7 | 1 |
| 130 | In Situ Method for Determining Combination of Organic Compounds Interacting with Each Other on Silicon Oxide Surface. ECS Journal of Solid State Science and Technology, 2015, 4, P408-P414. | 0.9 | 1 |
| 131 | 4H-Silicon Carbide Wafer Surface after Chlorine Trifluoride Gas Etching. Materials Science Forum, 0, 924, 369-372. | 0.3 | 1 |
| 132 | High Temperature SiC Reactor Cleaning Using Chlorine Trifluoride Gas Achieved by Purified Pyrolytic Carbon Coating Film. Materials Science Forum, 0, 963, 141-145. | 0.3 | 1 |
| 133 | Non-Plasma Dry Etcher Design for 200 mm-Diameter Silicon Carbide Wafer. Materials Science Forum, 0, 1004, 167-172. | 0.3 | 1 |
| 134 | Development of SiC Etching by Chlorine Fluoride Gas. Materials Science Forum, 0, 1004, 731-737. | 0.3 | 1 |
| 135 | Side wall water outlet design for silicon wafer wet cleaning bath. Materials Science in Semiconductor Processing, 2020, 110, 104970. | 1.9 | 1 |
| 136 | Temperature Influence on Organic Molecular Interaction on Silicon Oxide Surface In Situ Measured Utilizing a Quartz Crystal Microbalance. ECS Journal of Solid State Science and Technology, 2020, 9, 104007. | 0.9 | 1 |
| 137 | Room Temperature and Reduced Pressure Chemical Vapor Deposition of Silicon Carbide on Various Materials Surface. Advances in Chemical Engineering and Science, 2014, 04, 389-395. | 0.2 | 1 |
| 138 | Behavior of Viscous Liquid Byproduct Formed in Exhaust Tube by Silicon Carbide Epitaxial Growth. ECS Journal of Solid State Science and Technology, 2019, 8, P805-P810. | 0.9 | 1 |
| 139 | Water Motion in a Water Curtain Head for Cleaning a Large Glass Plate. Japanese Journal of Applied Physics, 2007, 46, 838-842. | 0.8 | 0 |
| 140 | Low Temperature Chemical Vapour Deposition of Polycrystalline Silicon Carbide Film Using Monomethylsilane Gas. , 0, , . | | 0 |
| 141 | Silicon Surface Morphology after Annealing in Ambient Hydrogen Containing a Trace Amount of Hydrogen Halide Gas. Japanese Journal of Applied Physics, 2011, 50, 025701. | 0.8 | 0 |
| 142 | Concentration of Three Organic Compounds Influencing each other on Silicon Surface. Solid State Phenomena, 2012, 187, 303-306. | 0.3 | 0 |
| 143 | Crystalline Defects in Silicon Wafer Caused by Prolonged High-Temperature Annealing in Nitrogen Atmosphere. Advanced Materials Research, 2013, 699, 445-449. | 0.3 | 0 |
| 144 | Amorphous Silicon Carbide Film Formation at Room Temperature by Monomethylsilane Gas. Materials Science Forum, 0, 740-742, 235-238. | 0.3 | 0 |

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|-----|---|-----|-----------|
| 145 | Off-Orientation Influence on C-Face (0001) 4H-SiC Surface Morphology Produced by Etching Using Chlorine Trifluoride Gas. Materials Science Forum, 2014, 778-780, 734-737. | 0.3 | 0 |
| 146 | Precipitates Caused in Silicon Wafers by Prolonged High-Temperature Annealing in Nitrogen Atmosphere. Materials Research Society Symposia Proceedings, 2014, 1591, 1. | 0.1 | 0 |
| 147 | In Situ Observation of Chemical Vapour Deposition Using Langasite Crystal Microbalance. , 0, , . | | 0 |
| 148 | Quick and Practical Cleaning Process for Silicon Carbide Epitaxial Reactor. Materials Science Forum, 0, 924, 96-99. | 0.3 | 0 |
| 149 | Silicon Epitaxial Reactor for Minimal Fab. , 2018, , . | | 0 |
| 150 | SiC Epitaxial Reactor Cleaning by ClF_3 Gas with the Help of Reaction Heat. Materials Science Forum, 0, 1004, 186-192. | 0.3 | 0 |
| 151 | Anticorrosive Behavior of Aluminum Nitride Surface Exposed to Chlorine Trifluoride Gas at High Temperatures. ECS Journal of Solid State Science and Technology, 2021, 10, 034006. | 0.9 | 0 |
| 152 | Chemical Conditions of SiCNO Film Exposed to ClF_3 Gas. ECS Journal of Solid State Science and Technology, 2021, 10, 103004. | 0.9 | 0 |
| 153 | Advance of Atomic Layer Deposition in Semiconductor Materials Manufacturing Process: Cleaning Technology for Thin Film Formation Reactor. Journal of the Vacuum Society of Japan, 2011, 54, 97-104. | 0.3 | 0 |
| 154 | Silicon Surface Morphology after Annealing in Ambient Hydrogen Containing a Trace Amount of Hydrogen Halide Gas. Japanese Journal of Applied Physics, 2011, 50, 025701. | 0.8 | 0 |
| 155 | Silicon Epitaxial Growth Rate and Transport Phenomena in a Vertical Stacked-Type Multi-Wafer Reactor. Japanese Journal of Applied Physics, 2012, 51, 026701. | 0.8 | 0 |
| 156 | Water Flow Improvement by Pinhole Outlet in Batch-Type Wet Cleaning Bath for Large-Diameter Wafers. ECS Journal of Solid State Science and Technology, 0, , . | 0.9 | 0 |